

**REMARKS**

In the above-identified office action the Examiner has rejected claims 9-13 over the Japanese patent to Furuya et al., the English abstract and the Computer translation of Furuya et al. Applicants have amended the claims so that they now recite that the wafer has a surface region, i.e., a DZ layer of several tens of  $\mu\text{m}$  deep and an adjacent central region. Applicants uniformly distribute the defects in the crystal wafer in the central region. Furuya teaches only about treatment of the DZ layer. As a result, Furuya does not make obvious the subject invention, as recited in the amended claims.

Claims 9-11 have been rejected over the U.S. patent to Bischoff et al. Bischoff also only teaches about treatment of the DZ layer and accordingly, for the reasons noted above, Applicants believe that claims 9-11, as amended, are now patentable in view of Bischoff et al.

Claims 9-13 have been rejected as unpatentable over Furuya et al., the English abstract and the Computer translation therefore, or Bischoff et al. in view of Iida et al. or Adachi et al. In so far as Bischoff, Adachi and Furuya only teach technology concerning the DZ layer, Applicants believe that the claims as amended are patentable thereover, for the same reasons as set forth above in the amended claims.

Applicants hereby request reconsideration and reexamination thereof.

With the above amendments and remarks, this application is considered ready for allowance and Applicants earnestly solicit an early notice of same. Should the Examiner be of the opinion that a telephone conference would expedite prosecution of the subject application, he is respectfully requested to call the undersigned at the below-listed number.

Respectfully submitted,

**WELSH & KATZ, LTD.**



Gerald T. Shekleton

Registration No. 27,466

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**WELSH & KATZ, LTD.**

120 South Riverside Plaza

22nd Floor

Chicago, Illinois 60606-3913

Telephone: 312/655-1500